Description

The DMNH4015SSD uses advanced trench technology

to provide excellent R_{DS(ON)}, low gate charge and

operation with gate voltages as low as 2.5V. This

device is suitable for use as a

Battery protection or in other Switching application.



SOP-8

General Features

 $V_{DS} = 40V I_{D} = 12A$

 $R_{DS(ON)}$ < 16m Ω @ V_{GS}=10 V

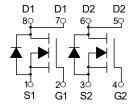
 $R_{DS(ON)}$ < 24m Ω @ V_{GS} =4.5V

Application

Battery protection

Load switch

Uninterruptible power supply



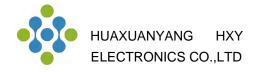
Dual N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
DMNH4015SSD	SOP-8	HXY MOSFET	3000

Absolute Maximum Ratings@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	40	V
V _{GS}	Gate-Source Voltage	<u>+</u> 20	V
I _D @T _A =25°C	Drain Current, V _{GS} @ 4.5V ³	12	А
I _D @T _A =70°C	Drain Current, V _{GS} @ 4.5V ³	7	А
Ірм	Pulsed Drain Current ¹	40	А
P _D @T _A =25°C	Total Power Dissipation	2.9	W
Тѕтс	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C
Rthj-a	Maximum Thermal Resistance, Junction- ambient ³	65	°C/W



Dual N-Channel Enhancement Mode MOSFET

Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	40	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS},I_{D}=250\mu A$	1	1.5	2.0	V
Drain-Source On-State Resistance	5	V _{GS} =10V, I _D =8A	-	12.0	16	mΩ
Diain-Source On-State Resistance	$R_{DS(ON)}$	V _{GS} =4.5V, I _D =4A	-	18.9	24	mΩ
Forward Transconductance	g FS	V _{DS} =5V,I _D =8A	33	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}	.,	-	964	-	PF
Output Capacitance	Coss	V_{DS} =20V, V_{GS} =0V, F=1.0MHz	-	109	-	PF
Reverse Transfer Capacitance	C _{rss}	r-1.0ivinz	-	96	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	5.5	-	nS
Turn-on Rise Time	t _r	V_{DD} =20V, R_L =2.5 Ω	-	14	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{GEN} =3 Ω	-	24	-	nS
Turn-Off Fall Time	t _f		-	12	-	nS
Total Gate Charge	Qg	V _{DS} =20V,I _D =8A,	-	22.9	-	nC
Gate-Source Charge	Q _{gs}	V_{DS} –20V, I_D –6A, V_{GS} =10V	-	3.5	-	nC
Gate-Drain Charge	Q_{gd}	v _{GS} -10v	-	5.3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =9A	-	8.0	1.2	V



Typical Electrical and Thermal Characteristics (Curves)

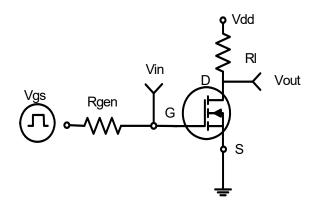


Figure 1:Switching Test Circuit

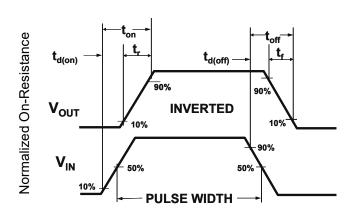


Figure 2:Switching Waveforms

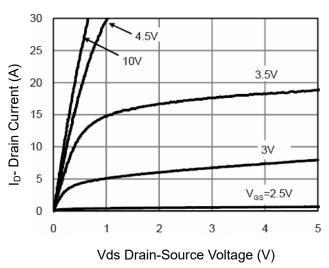


Figure 3 Output Characteristics

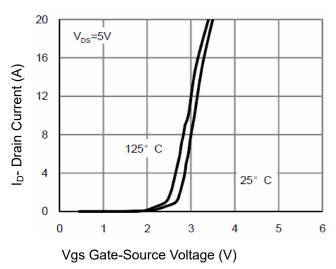


Figure 4 Transfer Characteristics

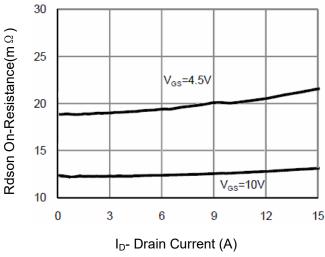


Figure 5 Drain-Source On-Resistance

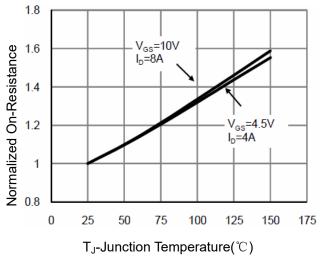
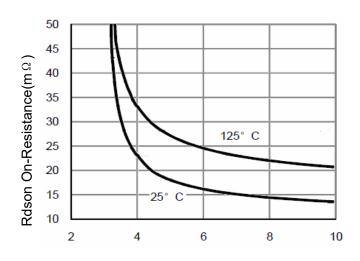


Figure 6 Drain-Source On-Resistance



Vgs Gate-Source Voltage (V)
Figure7 Rdson vs Vgs

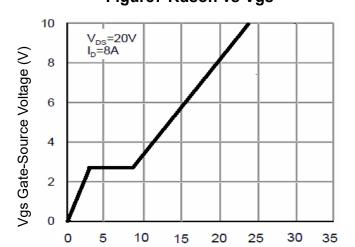


Figure 9 Gate Charge

Qg Gate Charge (nC)

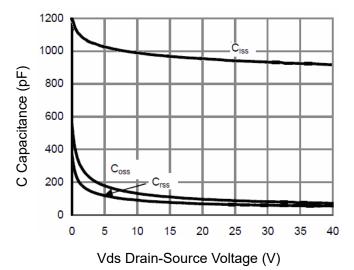
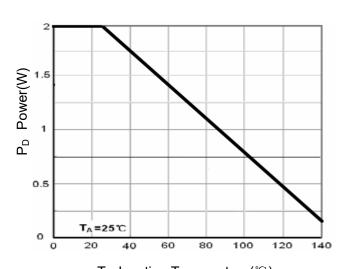
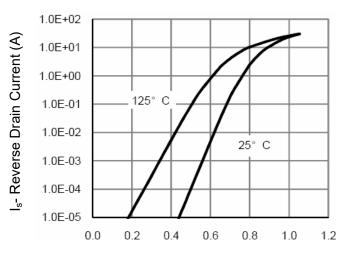


Figure 11 Capacitance vs Vds



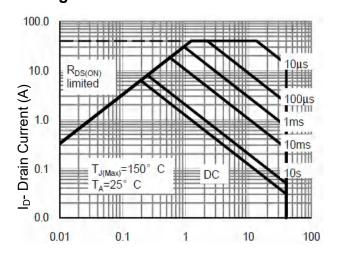
 T_J -Junction Temperature(${}^{\circ}\mathbb{C}$)





Vds Drain-Source Voltage (V)

Figure 10 Source- Drain Diode Forward

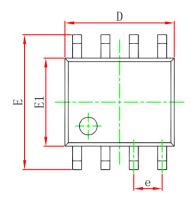


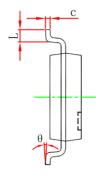
Vds Drain-Source Voltage (V)

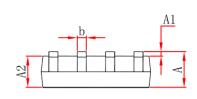
Figure 12 Safe Operation Area



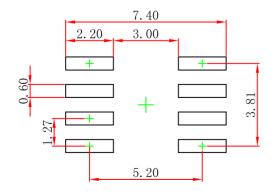
SOP-8 Package Outline Dimensions







Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
A	1. 350	1.750	0.053	0.069	
A1	0.100	0. 250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
c	0.170	0. 250	0.007	0.010	
D	4.800	5.000	0.189	0. 197	
e	1. 270 (BSC)		0.050 (BSC)		
E	5.800	6. 200	0. 228	0.244	
E1	3.800	4.000	0.150	0. 157	
L	0.400	1. 270	0.016	0.050	
θ	0°	8°	0°	8°	



- Note: 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.

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